

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266 <https://www.sciencedirect.com/science/article/pii/S0040609009014564>

Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262 https://globaljournals.org/GJSFR_Volume17/1-Stresses-Relaxation-Mechanism.pdf